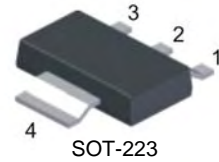


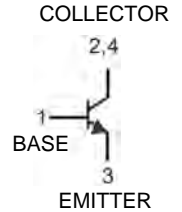
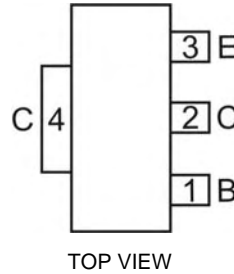
**Features**

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DZT953)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



**Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



Schematic and Pin Configuration

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	I <sub>C</sub>	6	A
Power Dissipation	P <sub>tot</sub>	1 (Note 3) 3 (Note 4)	W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  3. Device mounted on FR-4 PCB, pad layout as shown on page 4.
  4. The power which can be dissipated, assuming the device is mounted in a typical manner on a PCB with copper equal to 4 square inch minimum.

## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	200	—	—	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	100	—	—	V	I <sub>C</sub> = 10mA*, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6	—	—	V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CBO</sub>	—	—	10 1	nA μA	V <sub>CB</sub> = 150V, I <sub>E</sub> = 0 V <sub>CB</sub> = 150V, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C
Emitter Cutoff Current	I <sub>EBO</sub>	—	—	10	nA	V <sub>EB</sub> = 6V, I <sub>C</sub> = 0
<b>ON CHARACTERISTICS</b>						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	—	50 150 340	mV	I <sub>C</sub> = 0.1A, I <sub>B</sub> = 5mA* I <sub>C</sub> = 2A, I <sub>B</sub> = 100mA* I <sub>C</sub> = 5A, I <sub>B</sub> = 500mA*
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	—	1250	mV	I <sub>C</sub> = 5A, I <sub>B</sub> = 500mA*
Base-Emitter Turn-On Voltage	V <sub>BE(ON)</sub>	—	—	1100	mV	I <sub>CE</sub> = 5A, V <sub>CE</sub> = 2V*
DC Current Gain	h <sub>FE</sub>	100 100 50 20	—	— 300 — —	—	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 2V* I <sub>C</sub> = 2A, V <sub>CE</sub> = 2V* I <sub>C</sub> = 4A, V <sub>CE</sub> = 2V* I <sub>C</sub> = 10A, V <sub>CE</sub> = 2V*
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Current Gain-Bandwidth Product	f <sub>T</sub>	—	130	—	MHz	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 10V, f = 50MHz
Output Capacitance	C <sub>obo</sub>	—	35	—	pF	V <sub>CB</sub> = 10V, f = 1MHz
<b>SWITCHING CHARACTERISTICS</b>						
Switching Times	t <sub>on</sub> t <sub>off</sub>	—	50 1650	—	ns ns	I <sub>C</sub> = 1A, V <sub>CC</sub> = 10V I <sub>B1</sub> = I <sub>B2</sub> = 100mA

\* Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%

## Typical Characteristics @T<sub>amb</sub> = 25°C unless otherwise specified

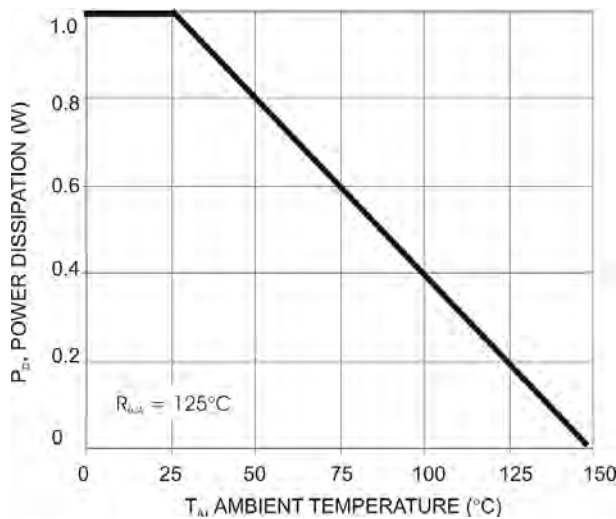


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

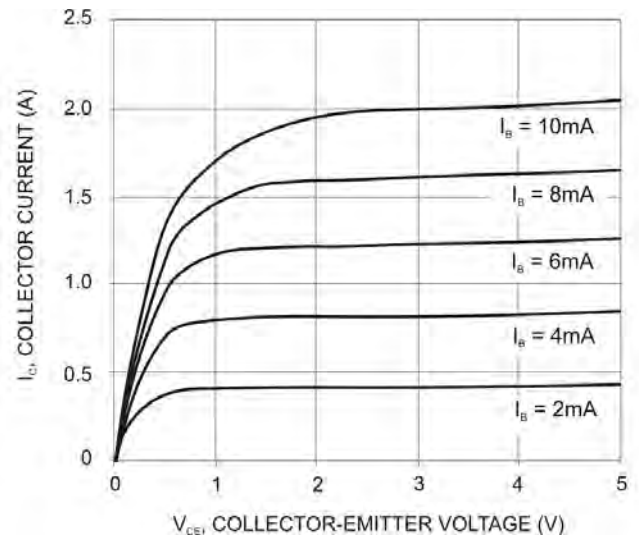


Fig. 2 Collector Current vs. Collector Emitter-Voltage

Notes: 3. Device mounted on FR-4 PCB, pad layout as shown on page 4.

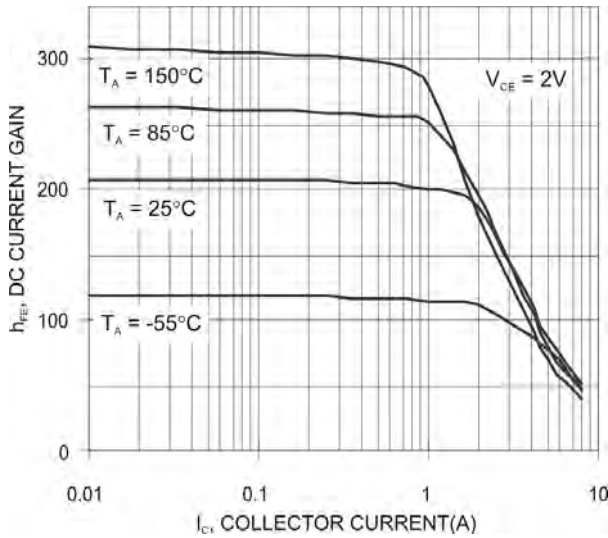


Fig. 3 Typical DC Current Gain vs. Collector Current

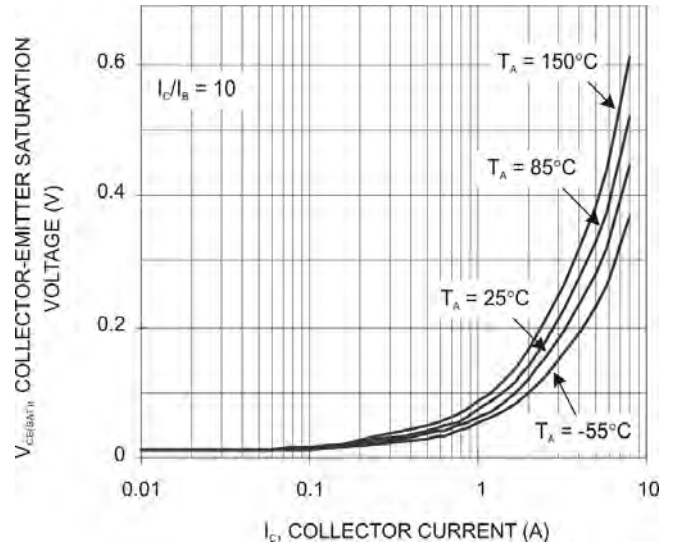


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

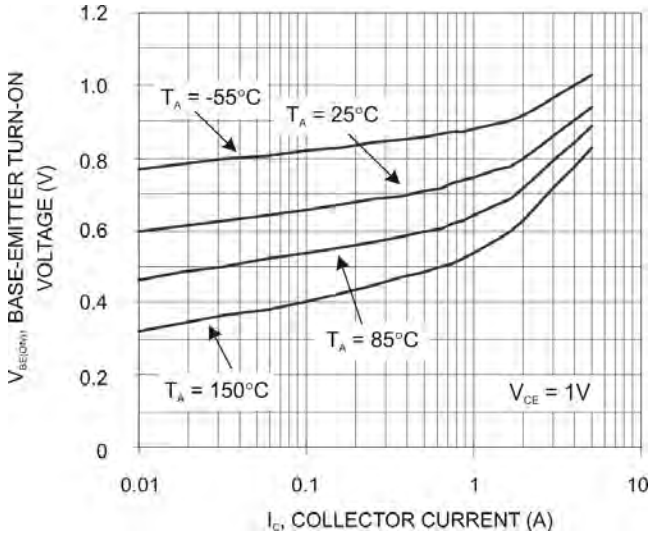


Fig. 5 Base-Emitter Turn-On Voltage vs. Collector Current

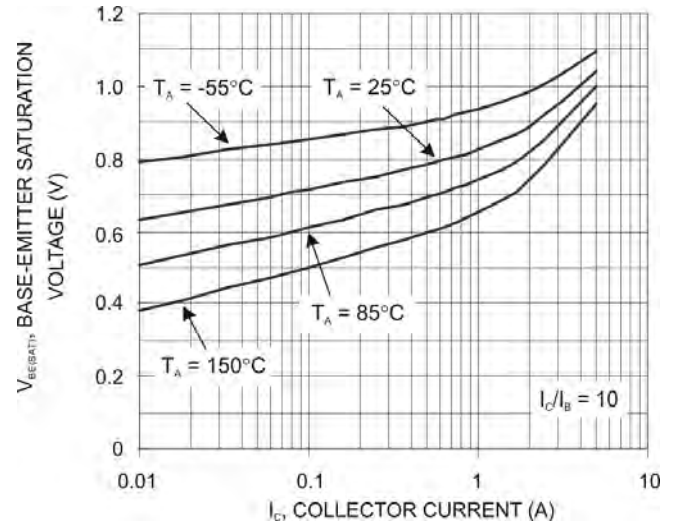


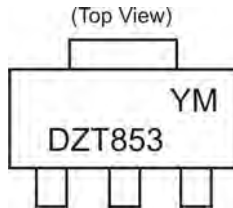
Fig. 6 Base-Emitter Saturation Voltage vs. Collector Current

## Ordering Information (Note 5)

Device	Packaging	Shipping
DZT853-13	SOT-223	2500/Tape & Reel

Notes: 5. Packaging Details as shown on page 4, or go to our website at <http://www.diodes.com/ap2007.pdf>.

## Marking Information



DZT853 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: T = 2006  
 M = Month ex: 9 = September

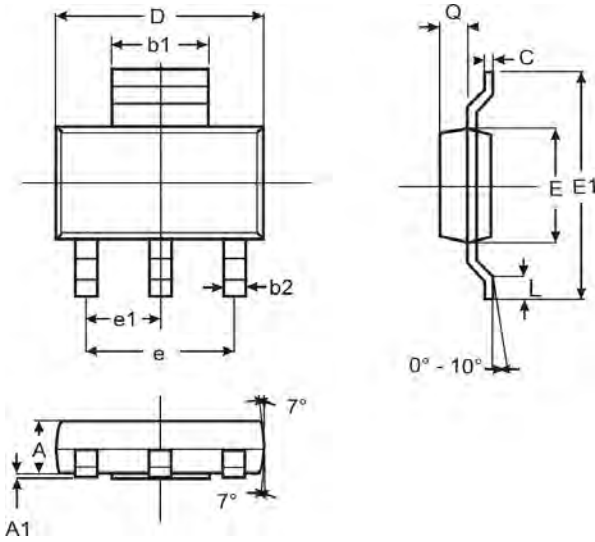
### Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

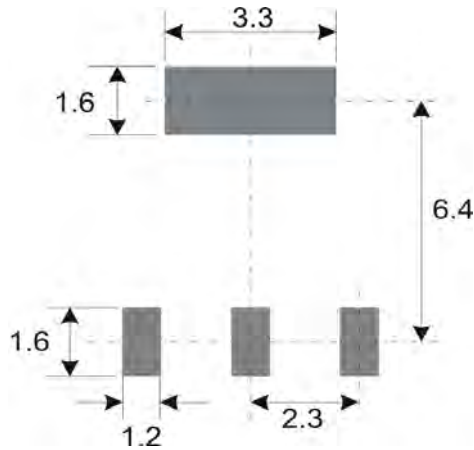
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Package Outline Dimensions



SOT-223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

## Suggested Pad Layout: (Based on IPC-SM-782)



(Unit:mm)

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